



BD238

PNP EPITAXIAL SILICON TRANSISTOR

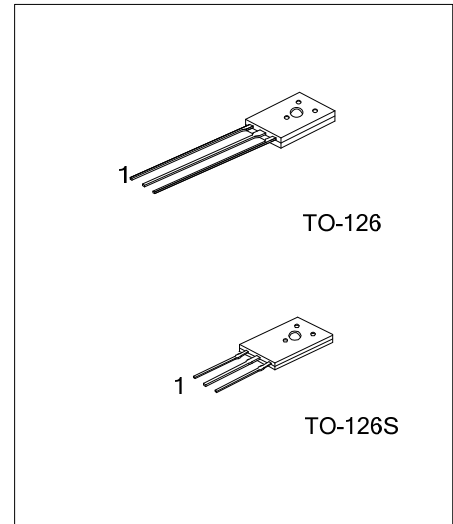
-80V, PNP TRANSISTOR

DESCRIPTION

The UTC **BD238** is a PNP epitaxial planar transistor, it uses UTC's advanced technology to provide the customers with high DC current gain and high collector-emitter breakdown voltage, etc.

FEATURES

- * High DC current gain
- * High collector-emitter breakdown voltage



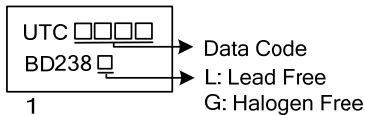
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
BD238L-T60-K	BD238G-T60-K	TO-126	E	C	B	Bulk
BD238L-T6S-K	BD238G-T6S-K	TO-126S	E	C	B	Bulk

Note: Pin assignment: E: Emitter B: Base C: Collector

<p>BD238L-T60-K</p> <ul style="list-style-type: none"> (1) Packing Type (2) Package Type (3) Green Package 	<ul style="list-style-type: none"> (1) K: Bulk (2) T60: TO-126, T6S: TO-126S (3) L: Lead Free, G: Halogen Free and Lead Free
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MARKING





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■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

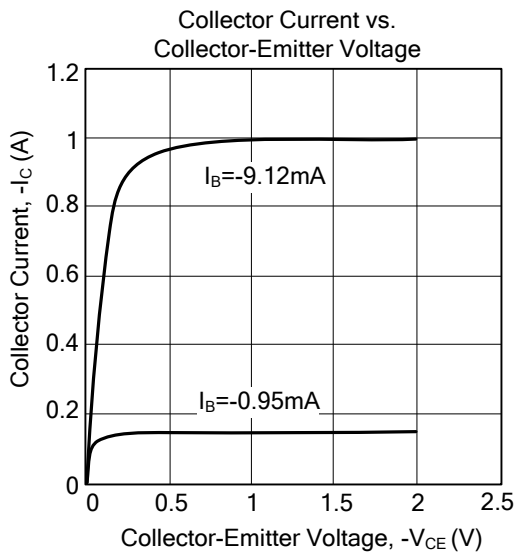
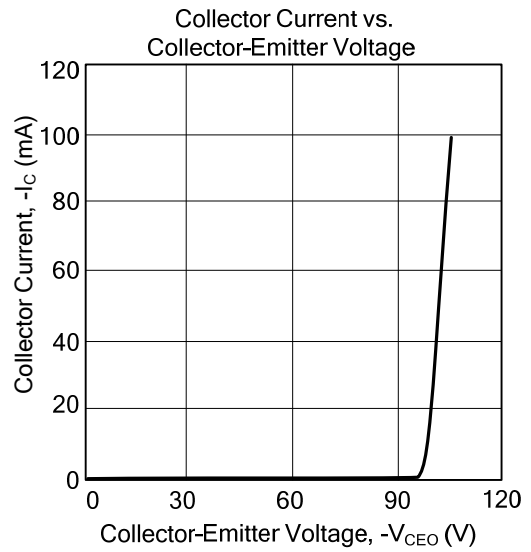
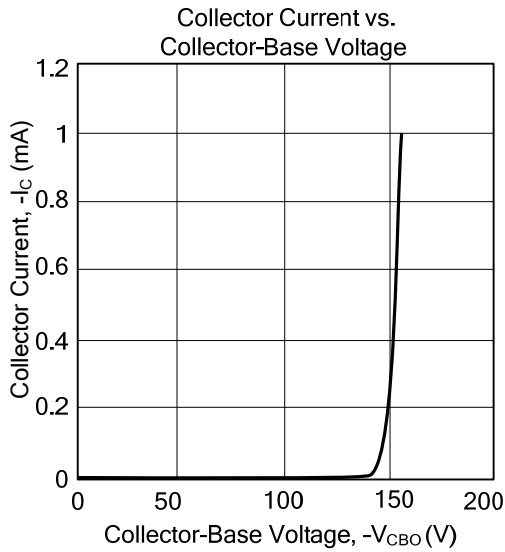
PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-2	A
Collector Power Dissipation	P_C	1.25	W
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~150	$^{\circ}\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-1\text{mA}, I_E=0$	-100			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-100\text{mA}, I_B=0$	-80			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_C=-1\text{mA}, I_E=0$	-5			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-100\text{V}, I_E=0$			-100	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-1	mA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-2\text{V}, I_C=-150\text{mA}$	40			
	$h_{FE(2)}$	$V_{CE}=-2\text{V}, I_C=-1\text{A}$	25			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-1\text{A}, I_B=-100\text{mA}$			-0.6	V
Transition Frequency	f_T	$V_{CE}=-10\text{V}, I_C=-250\text{mA}, f=10\text{MHz}$	3			MHz

■ TYPICAL CHARACTERISTICS



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